

# Si PNP TRANSISTOR

2SA573, 2SA574

EPOXY MOLDED, AUDIO AMP., RF AMP., SWITCHING

## ■ ABSOLUTE MAXIMUM RATINGS (Ta : 25°C)

		2SA573	2SA574	
COLLECTOR-BASE VOLTAGE	$V_{CBO}$	-30	-60	V
COLLECTOR-EMITTER VOLTAGE	$V_{CEO}$	-25	-50	V
EMITTER-BASE VOLTAGE	$V_{EBO}$	-5	-5	V
COLLECTOR CURRENT	$I_C$	-100	-100	mA
POWER DISSIPATION	$P_C$	300	300	mW
JUNCTION TEMPERATURE	$T_j$	125	125	°C
STORAGE TEMPERATURE	$T_{stg}$	-55~+125	-55~+125	°C

## ■ ELECTRICAL CHARACTERISTICS (Ta : 25°C)

PARAMETER	SYM.	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
COLLECTOR CUTOFF CURRENT	$I_{CBO}$	$V_{CB} : -20V, I_E : 0$			-100	nA
STATIC FWD. CUR. TRANSFER RATIO	$h_{FE}$	$V_{CE} : -6V, I_C : -1mA, \text{NOTE 1}$	30		800	
TRANSITION FREQUENCY	$f_T$	$V_{CE} : -10V, I_E : 2mA$	80	150		MHz
COLLECTOR OUTPUT CAPACITANCE	$C_{ob}$	$V_{CB} : -10V, I_E : 0, f : 1MHz$		4	10	pF
BASE-COLLECTOR TIME CONSTANT	$C_{eTb'b}$	$V_{CB} : -10V, I_E : 2mA, f : 31.9MHz$		50	150	ps
COLLECTOR-EMITTER SATURATION VOLTAGE	$V_{CE(sat)}$	$I_C : -50mA, I_B : -10mA$			-0.3	V
BASE-EMITTER SATURATION VOLTAGE	$V_{BE(sat)}$	$I_C : -50mA, I_B : -10mA$			-1.0	V

NOTE 1 : ACCORDING TO THE VALUE OF  $h_{FE}$ , THE DEVICES ARE CLASSIFIED AS FOLLOWS.

- RANK 1 : 30~70
- RANK 2 : 60~120
- RANK 3 : 90~180
- RANK 4 : 150~350
- RANK 5 : 250~500
- RANK 6 : 400~800

NOTE 2 : FOR COMPLEMENTARY CIRCUITS USING **2SA573** AND **2SA574**, NPN DEVICES TYPE **2SC950** AND **2SC951** ARE RESPECTIVELY AVAILABLE FOR REQUEST.

